

# RJK1560DPP-M0

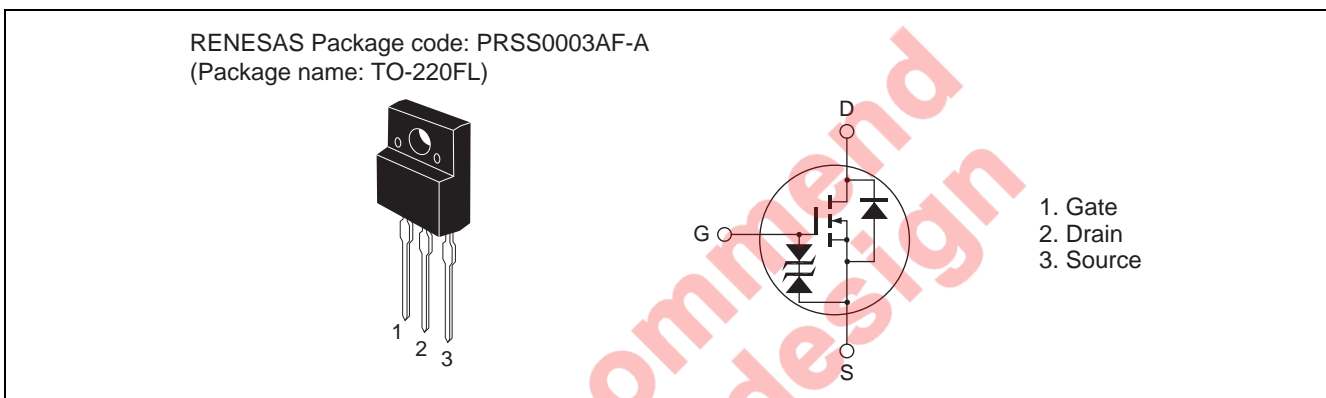
Silicon N Channel MOS FET  
High Speed Power Switching

R07DS0270EJ0100  
Rev.1.00  
Mar 07, 2011

## Features

- Capable of 2.5 V gate drive
- Low on-resistance  
 $R_{DS(on)} = 0.043 \Omega$  typ. (at  $I_D = 10$  A,  $V_{GS} = 4$  V,  $T_a = 25^\circ\text{C}$ )
- Low leakage current
- High speed switching

## Outline



## Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

| Item  | Symbol                           | Ratings     | Unit                      |
|---|----------------------------------|-------------|---------------------------|
| Drain to source voltage                     | $V_{DSS}$                        | 150         | V                         |
| Gate to source voltage                      | $V_{GSS}$                        | $\pm 10$    | V                         |
| Drain current                               | $I_D$                            | 20          | A                         |
| Drain peak current                          | $I_{D(pulse)}$ <sup>Note1</sup>  | 80          | A                         |
| Body-drain diode reverse drain current      | $I_{DR}$                         | 20          | A                         |
| Body-drain diode reverse drain peak current | $I_{DR(pulse)}$ <sup>Note1</sup> | 80          | A                         |
| Avalanche current                           | $I_{AP}$ <sup>Note3</sup>        | 16          | A                         |
| Avalanche energy                            | $E_{AR}$ <sup>Note3</sup>        | 19.2        | mJ                        |
| Channel dissipation                         | $P_{ch}$ <sup>Note2</sup>        | 28.5        | W                         |
| Channel to case thermal impedance           | $\theta_{ch-c}$                  | 4.38        | $^\circ\text{C}/\text{W}$ |
| Channel temperature                         | $T_{ch}$                         | 150         | $^\circ\text{C}$          |
| Storage temperature                         | $T_{stg}$                        | -55 to +150 | $^\circ\text{C}$          |

Notes: 1.  $PW \leq 10 \mu\text{s}$ , duty cycle  $\leq 1\%$   
 2. Value at  $T_c = 25^\circ\text{C}$   
 3.  $ST_{ch} = 25^\circ\text{C}$ ,  $T_{ch} \leq 150^\circ\text{C}$

## Electrical Characteristics

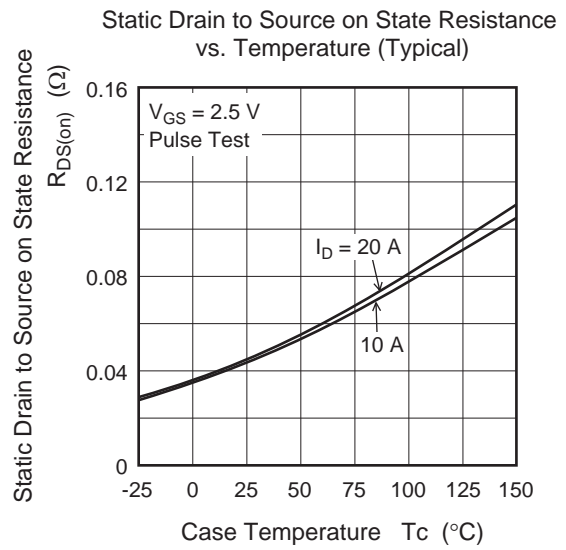
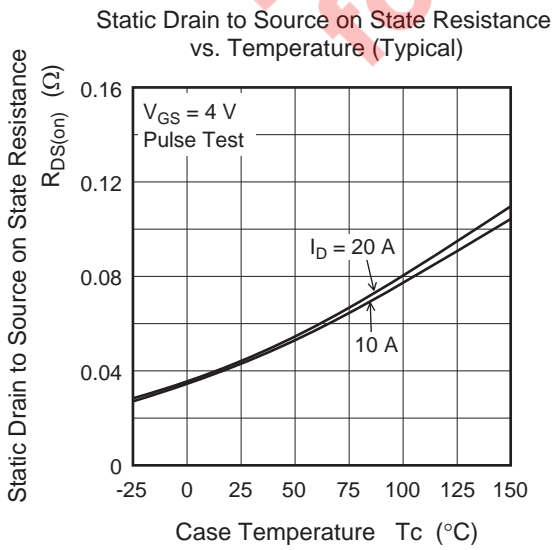
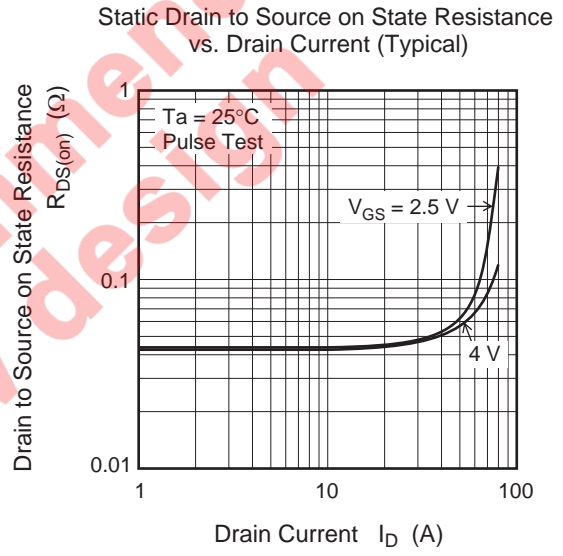
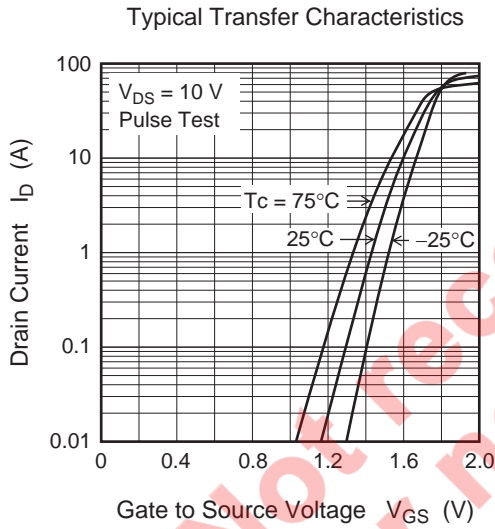
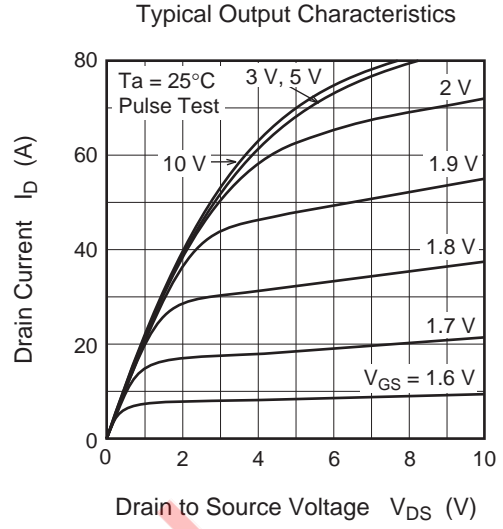
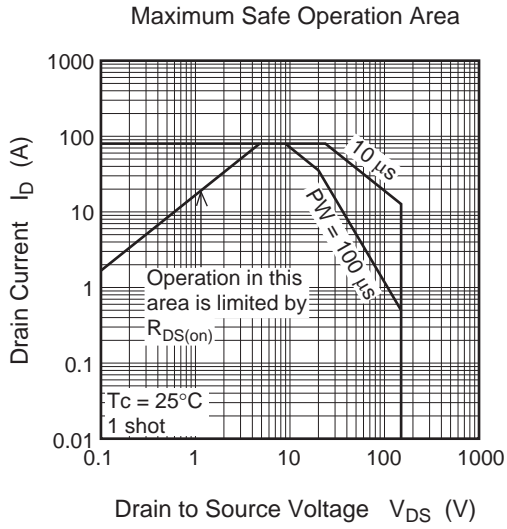
(Ta = 25°C)

| Item                                       | Symbol        | Min      | Typ   | Max      | Unit          | Test conditions  |
|--|---------------|----------|-------|----------|---------------|--|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$ | 150      | —     | —        | V             | $I_D = 10 \text{ mA}$ , $V_{GS} = 0$   |
| Gate to source breakdown voltage           | $V_{(BR)GSS}$ | $\pm 10$ | —     | —        | V             | $I_G = \pm 100 \mu\text{A}$ , $V_{DS} = 0$                                   |
| Zero gate voltage drain current            | $I_{DSS}$     | —        | —     | 1        | $\mu\text{A}$ | $V_{DS} = 150 \text{ V}$ , $V_{GS} = 0$                                      |
| Gate to source leak current                | $I_{GSS}$     | —        | —     | $\pm 10$ | $\mu\text{A}$ | $V_{GS} = \pm 10 \text{ V}$ , $V_{DS} = 0$                                   |
| Gate to source cutoff voltage              | $V_{GS(off)}$ | 0.5      | —     | 1.5      | V             | $V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$                               |
| Static drain to source on state resistance | $R_{DS(on)}$  | —        | 0.043 | 0.060    | $\Omega$      | $I_D = 10 \text{ A}$ , $V_{GS} = 4 \text{ V}$ <sup>Note4</sup>               |
|  | $R_{DS(on)}$  | —        | 0.044 | 0.070    | $\Omega$      | $I_D = 10 \text{ A}$ , $V_{GS} = 2.5 \text{ V}$ <sup>Note4</sup>             |
| Input capacitance                          | $C_{iss}$     | —        | 6720  | —        | pF            | $V_{DS} = 25 \text{ V}$  |
| Output capacitance                         | $C_{oss}$     | —        | 205   | —        | pF            | $V_{GS} = 0$   |
| Reverse transfer capacitance               | $C_{rss}$     | —        | 102   | —        | pF            | $f = 1 \text{ MHz}$  |
| Turn-on delay time                         | $t_{d(on)}$   | —        | 43    | —        | ns            | $I_D = 10 \text{ A}$   |
| Rise time                                  | $t_r$         | —        | 79    | —        | ns            | $V_{GS} = 4 \text{ V}$   |
| Turn-off delay time                        | $t_{d(off)}$  | —        | 250   | —        | ns            | $R_L = 7.5 \Omega$   |
| Fall time                                  | $t_f$         | —        | 117   | —        | ns            | $R_g = 10 \Omega$  |
| Total gate charge                          | $Q_g$         | —        | 52    | —        | nC            | $V_{DD} = 120 \text{ V}$   |
| Gate to source charge                      | $Q_{gs}$      | —        | 13    | —        | nC            | $V_{GS} = 4 \text{ V}$   |
| Gate to drain charge                       | $Q_{gd}$      | —        | 14    | —        | nC            | $I_D = 20 \text{ A}$   |
| Body-drain diode forward voltage           | $V_{DF}$      | —        | 0.83  | 1.30     | V             | $I_F = 20 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>                         |
| Body-drain diode reverse recovery time     | $t_{rr}$      | —        | 75    | —        | ns            | $I_F = 20 \text{ A}$ , $V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu\text{s}$ |

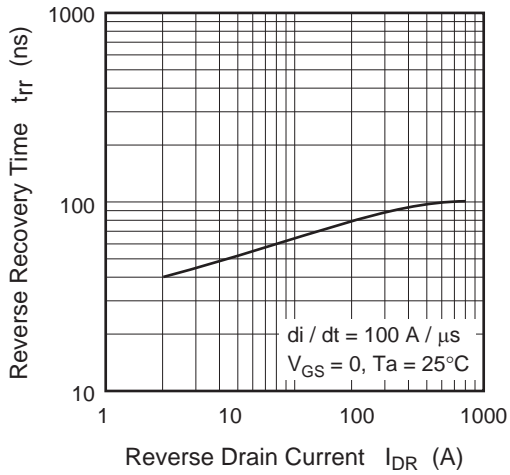
Notes: 4. Pulse test

Not recommended  
for new designs

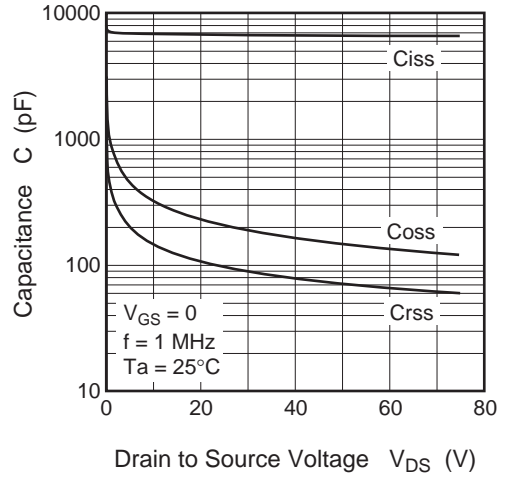
Main Characteristics



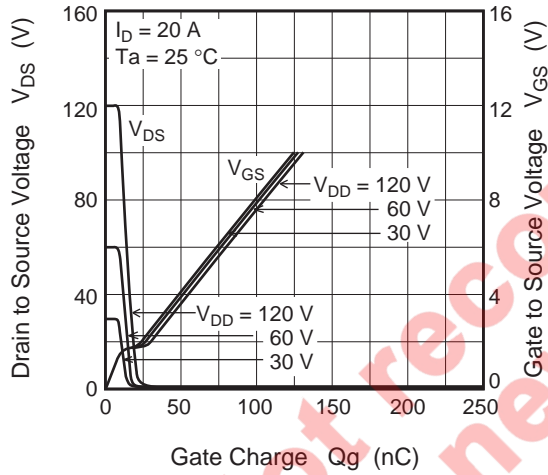
Body-Drain Diode Reverse Recovery Time (Typical)



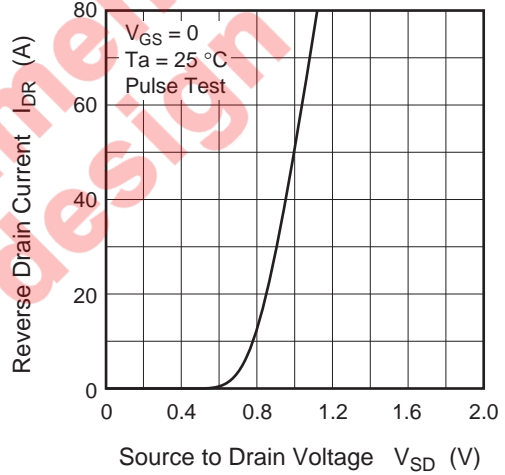
Typical Capacitance vs. Drain to Source Voltage



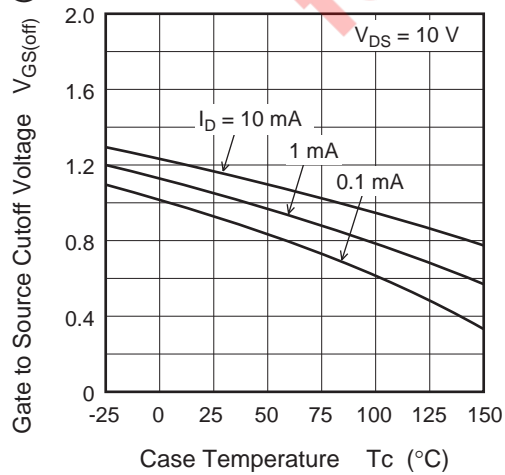
Dynamic Input Characteristics (Typical)



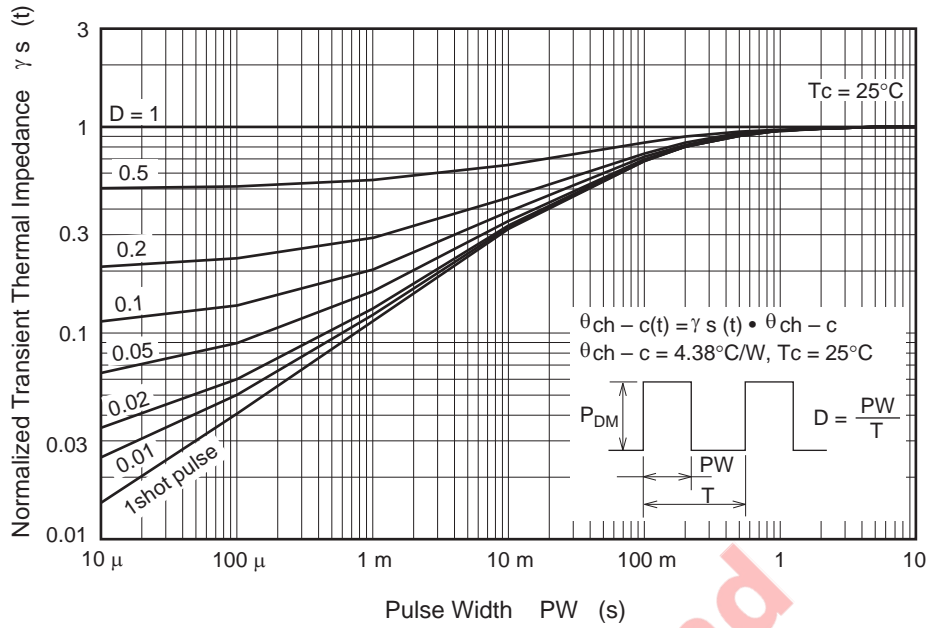
Reverse Drain Current vs. Source to Drain Voltage (Typical)



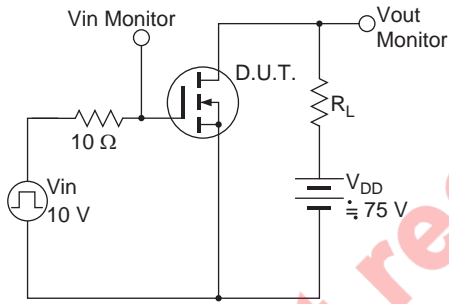
Gate to Source Cutoff Voltage vs. Case Temperature (Typical)



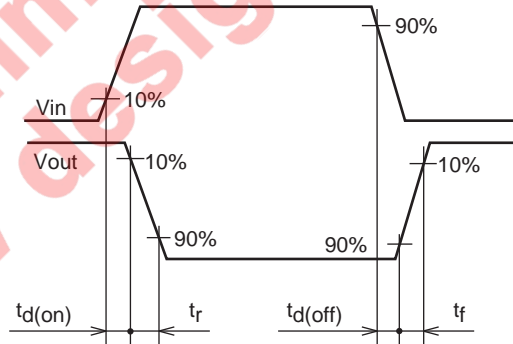
Normalized Transient Thermal Impedance vs. Pulse Width



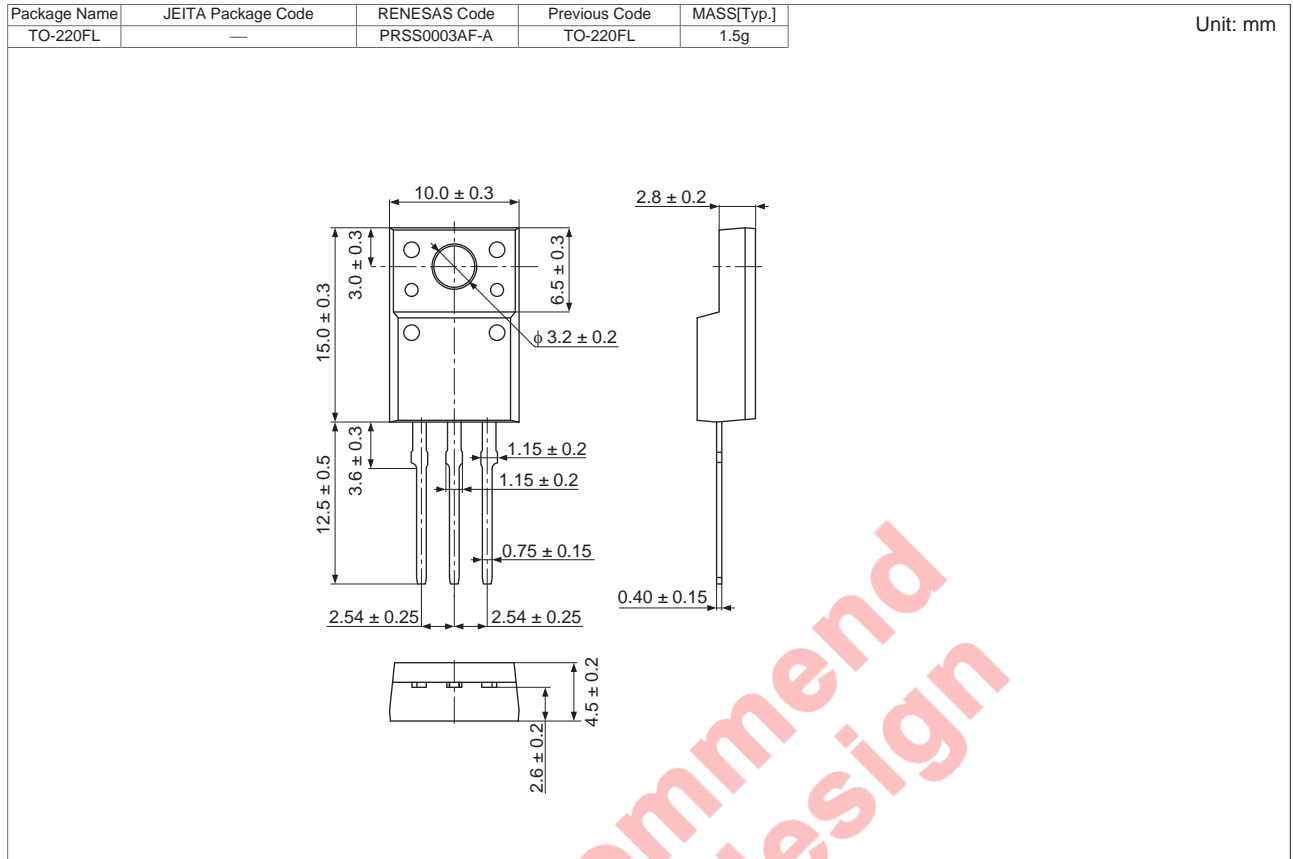
Switching Time Test Circuit



Waveform



### Package Dimensions



### Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK1560DPP-M0-T2      | 600 pcs  | Box (Tube)         |

Not recommend  
for new design

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